

150V NPN SILICON PLANAR MEDIUM POWER TRANSISTOR IN SOT89

Features

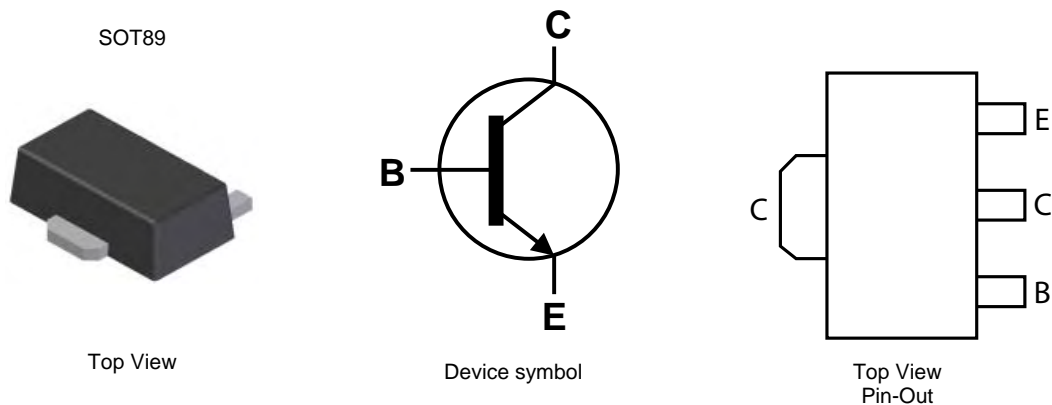
- $BV_{CEO} > 150V$
- High Current Capability Maximum Continuous Current $I_C = 1A$
- Low Saturation Voltage $V_{CE(sat)} < 300mV @ 0.5A$
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound
- Moisture Sensitivity: Level 1 per J-STD-020
- UL Flammability Rating 94V-0
- Terminals: Matte Tin Finish (e3)
- Weight: 0.052 grams (Approximate)

Application

- Power MOSFET Gate Driving
- Low Loss Power Switching

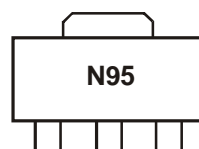


Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FCX495TA	N95	7	12	1000
FCX495TC	N95	13	12	4000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



N95 = Product Type Marking Code

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

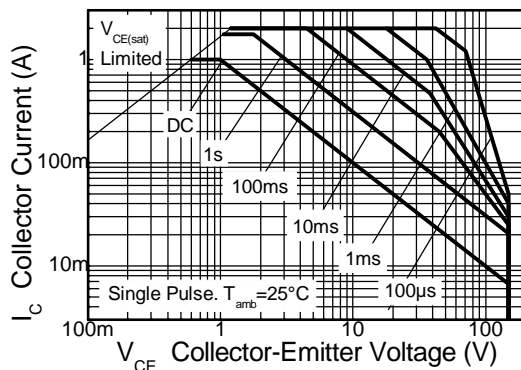
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	170	V
Collector-Emitter Voltage	V _{CEO}	150	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	I _C	1	A
Peak Pulse Current	I _{CM}	2	A
Continuous Base Current	I _B	200	mA

Thermal Characteristics

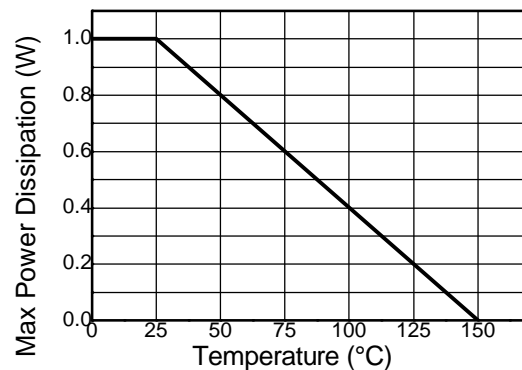
Characteristic	Symbol	Value	Unit
Collector Power Dissipation	P _D	1	W
Thermal Resistance, Junction to Ambient Air (Note 5)	R _{θJA}	125	°C/W
Thermal Resistance, Junction to Leads (Note 6)	R _{θJL}	10.01	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

Notes: 5. For the device mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
6. Thermal resistance from junction to solder-point (on the exposed collector pad).

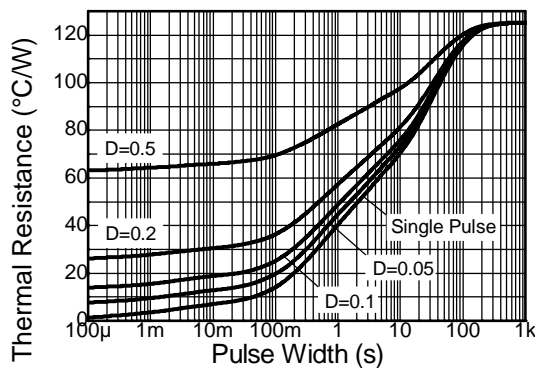
Thermal Characteristics



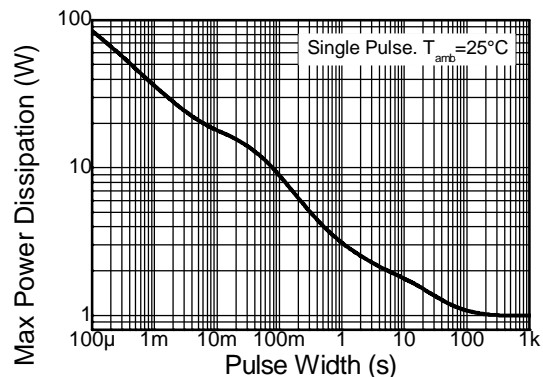
Safe Operating Area



Derating Curve



Transient Thermal Impedance



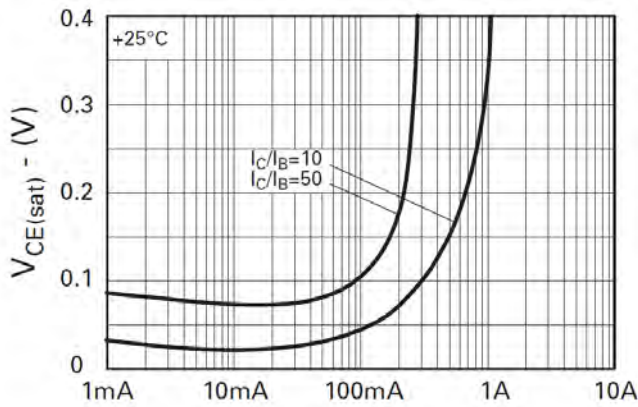
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

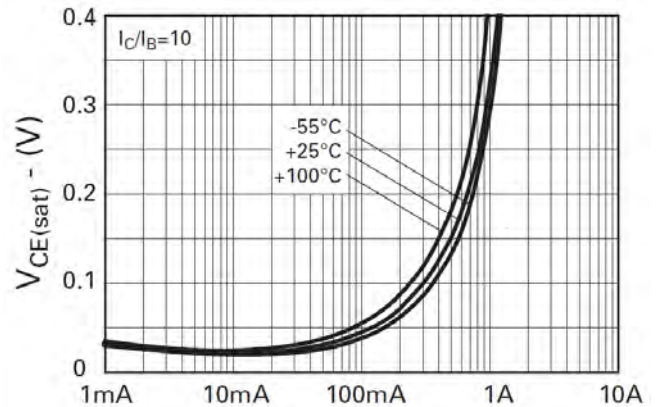
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	170	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 7)	BV _{CEO}	150	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	6	—	—	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	-	—	100	nA	V _{CB} = 150V
Emitter Cutoff Current	I _{EBO}	-	—	100	nA	V _{EB} = 5V
Emitter Cutoff Current	I _{CES}	-	—	100	nA	V _{CE} = 150V
DC current transfer Static ratio (Note 7)	h _{FE}	100	—	—	—	I _C = 1mA, V _{CE} = 10V
		100	—	300	—	I _C = 250mA, V _{CE} = 10V
		50	—	—	—	I _C = 500mA, V _{CE} = 10V
		10	—	—	—	I _C = 1A, V _{CE} = 10V
Collector-Emitter Saturation Voltage (Note 7)	V _{CE(sat)}	—	—	0.2	V	I _C = 250mA, I _B = 25mA
		—	—	0.3	V	I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage (Note 7)	V _{BE(sat)}	—	—	1.0	V	I _C = 500mA, I _B = 50mA
Base-Emitter Turn-on Voltage (Note 7)	V _{BE(on)}	—	—	1.0	V	I _C = 500mA, V _{CE} = 10V
Transitional Frequency	f _T	100	—	-	MHz	I _C = 50mA, V _{CE} = 10V f = 100MHz
Output capacitance	C _{obo}	—	—	10	pF	V _{CB} = 10V, f = 1MHz,

Notes: 7. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤ 2%.

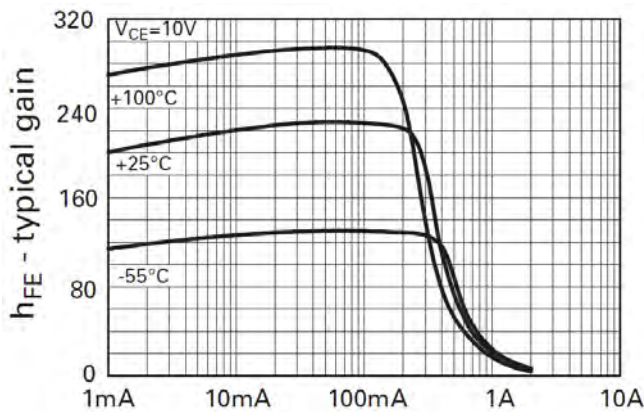
Typical Characteristics



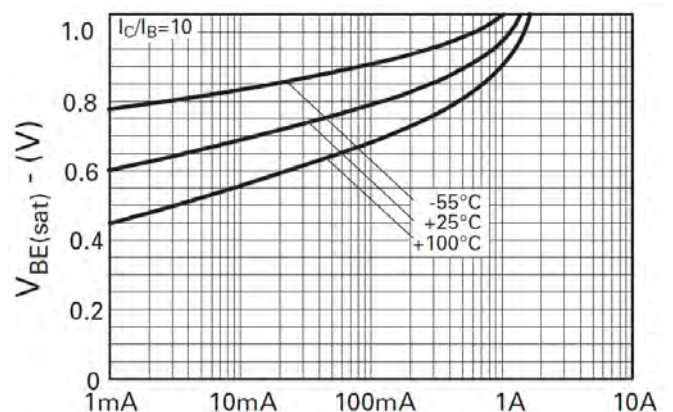
I_C - Collector current
 $V_{CE(sat)}$ vs. I_C



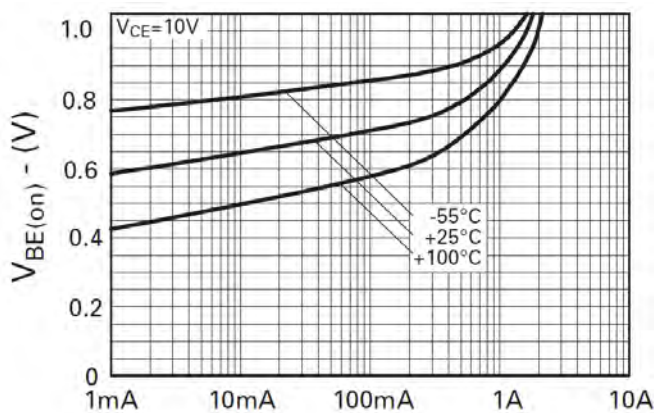
I_C - Collector current
 $V_{CE(sat)}$ vs. I_C



I_C - Collector current
 h_{FE} vs. I_C

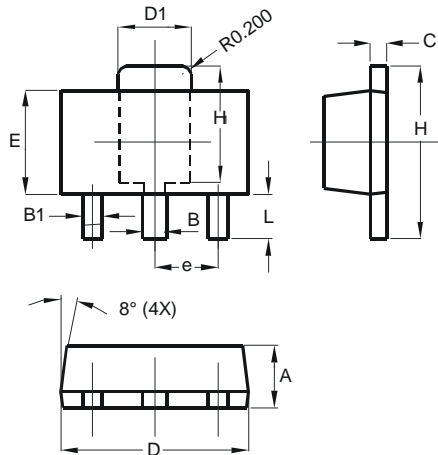


I_C - Collector current
 $V_{BE(sat)}$ vs. I_C



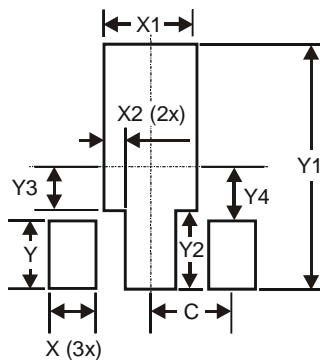
I_C - Collector current
 $V_{BE(on)}$ vs. I_C

Package Outline Dimensions



SOT89		
Dim	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.44
D	4.40	4.60
D1	1.62	1.83
E	2.29	2.60
e	1.50 Typ	
H	3.94	4.25
H1	2.63	2.93
L	0.89	1.20
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1.500

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